## Abstract Submitted for the MAR13 Meeting of The American Physical Society

Formation and coalescence of surface domains introduced by metal deposition on a stepped Si(111) surface<sup>1</sup> F.K. MEN, A.L. CHIN, C.P. CHANG, Department of Physics, National Chung Cheng University, Chia-Yi 621, Taiwan, ROC — By depositing sub-monolayer Au atoms onto a stepped Si(111)- $(7\times7)$  surface at  $600^{\circ}$ C, stripes of  $(5\times2)$  domain form on the upper step edges of most terraces. Upon continued annealing at a higher temperature, most of the terraces transform into either Au-free  $(7\times7)$  terraces or fully reconstructed  $(5\times2)$  terraces. After analyzing the distance distribution between neighboring  $(5\times2)$  terraces we detect the presence of an optimal distance separating  $(5\times2)$  terraces. This optimal distance, controllable via the Au coverage, can be explained by the minimization of long-range strain relaxation energy of a system consisted of alternating domains. The ability of tuning surface domain structure through metal deposition provides a new way of manipulating surface morphology in the nanometer-scale range.

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F.K. Men Department of Physics, National Chung Cheng University, Chia-Yi 621, Taiwan, ROC

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